

isc Silicon PNP Power Transistors

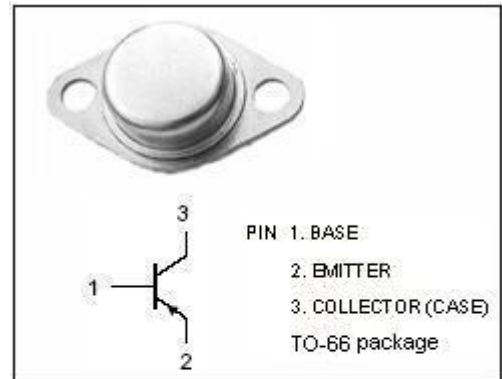
2N5611

DESCRIPTION

- DC Current Gain-
: $h_{FE} = 30-90 @ I_C = -2.5A$
- Wide Area of Safe Operation
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = -100V(\text{Min})$
- Complement to Type 2N5612

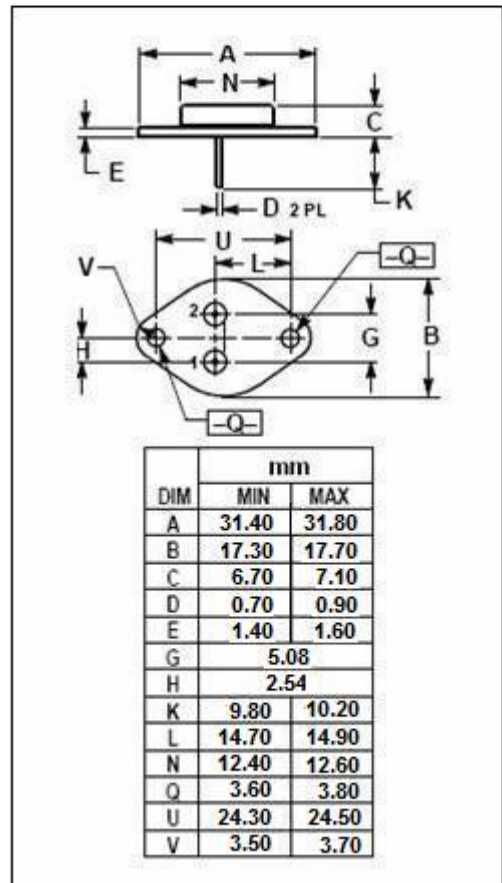
APPLICATIONS

- Designed for use in high frequency power amplifiers, audio power amplifier and drivers.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-5	A
P_C	Collector Power Dissipation@ $T_C=25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	6.0	$^\circ\text{C/W}$

isc Silicon PNP Power Transistors**2N5611****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -50\text{mA}$; $I_B = 0$	-100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2.5\text{A}$; $I_B = -0.25\text{A}$		-0.75	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -2.5\text{A}$; $I_B = -0.25\text{A}$		-1.45	V
I_{CEO}	Collector Cutoff Current	$V_{CE} = -100\text{V}$; $I_B = 0$		-1.0	mA
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120\text{V}$; $I_E = 0$		-0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -6\text{V}$; $I_C = 0$		-0.1	mA
h_{FE}	DC Current Gain	$I_C = -2.5\text{A}$; $V_{CE} = -5\text{V}$	30	90	
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}$; $V_{CE} = -10\text{V}$	50		MHz